



### Description

The XPX7401RD uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

$V_{DS} = -30V, I_D = -90A$

$R_{DS(ON)} = 5.0m\Omega @ V_{GS} = -10V$

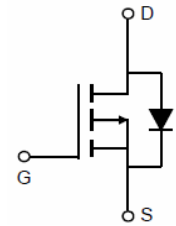
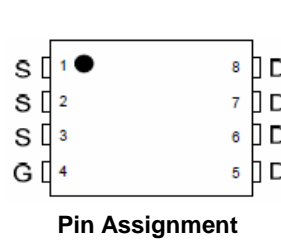
$R_{DS(ON)} = 6.5m\Omega @ V_{GS} = -4.5V$

### General Features

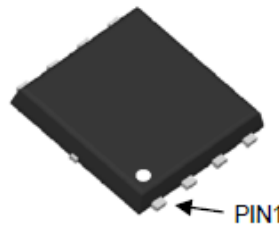
- High density cell design for ultra low  $R_{dson}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high  $E_{AS}$
- Excellent package for good heat dissipation

### Application

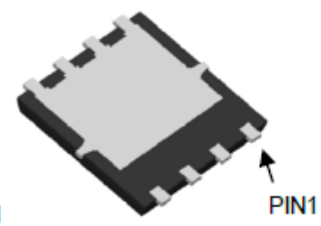
- Load switch
- Battery protection



Top View



Bottom View



### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
XPX7401RD	XPX7401RD	DFN5X6-8L	-	-	5000

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	-90	A
Drain Current-Continuous( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	-64	A
Pulsed Drain Current	$I_{DM}$	-280	A
Maximum Power Dissipation	$P_D$	65	W
Derating factor		0.6	W/ $^\circ C$
Single pulse avalanche energy <sup>(Note 5)</sup>	$E_{AS}$	450	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$
Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta JC}$	1.7	$^\circ C/W$

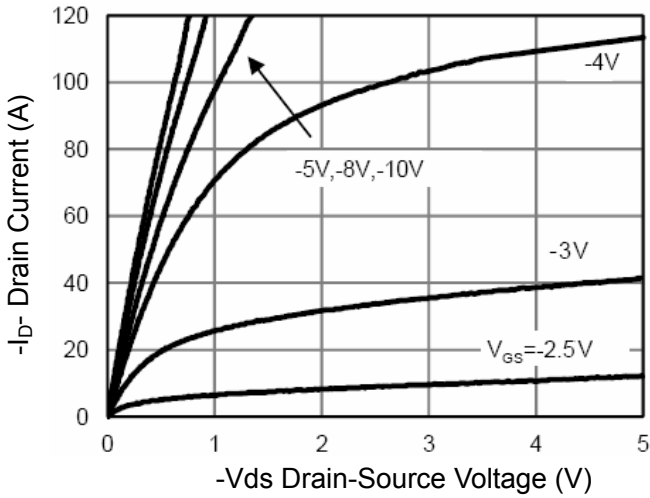
**Electrical Characteristics (T<sub>C</sub>=25 °C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-30		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1.0	-1.5	-2.2	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-20A	-	5.0	5.6	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-20A	-	6.5	8.0	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =-5V, I <sub>D</sub> =-20A	-	30	-	S
<b>Dynamic Characteristics</b> (Note4)						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, F=1.0MHz	-	5810	-	PF
Output Capacitance	C <sub>oss</sub>		-	650	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	550	-	PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-15V, I <sub>D</sub> =-20A V <sub>GS</sub> =-10V, R <sub>G</sub> =1.6Ω	-	16	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	13	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	40	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	10	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-15V, I <sub>D</sub> =-20A, V <sub>GS</sub> =-10V	-	62	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	15	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	19	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-20A	-		-1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	-90	A
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C, I <sub>F</sub> = -20A di/dt = 100A/μs (Note3)	-		24	nS
Reverse Recovery Charge	Q <sub>rr</sub>		-		68	nC

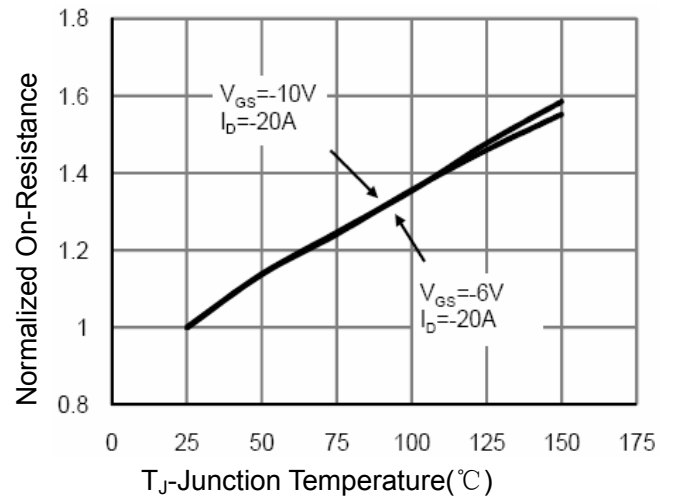
**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition : T<sub>J</sub>=25 °C, V<sub>DD</sub>=-20V, V<sub>G</sub>=-10V, L=0.5mH, R<sub>G</sub>=25Ω

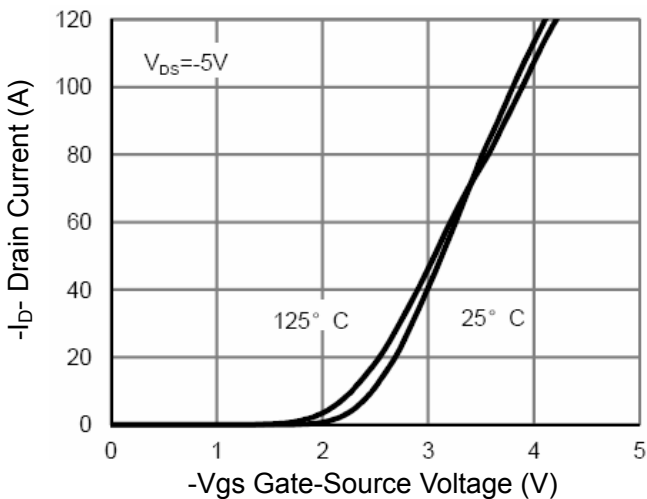
**Typical Electrical and Thermal Characteristics**



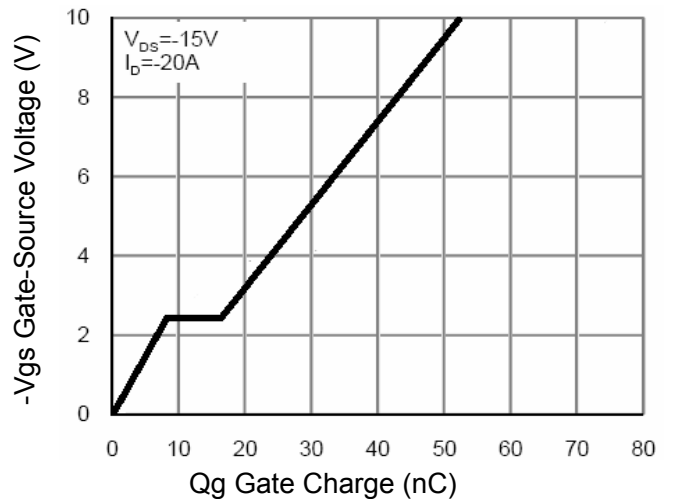
**Figure 1 Output Characteristics**



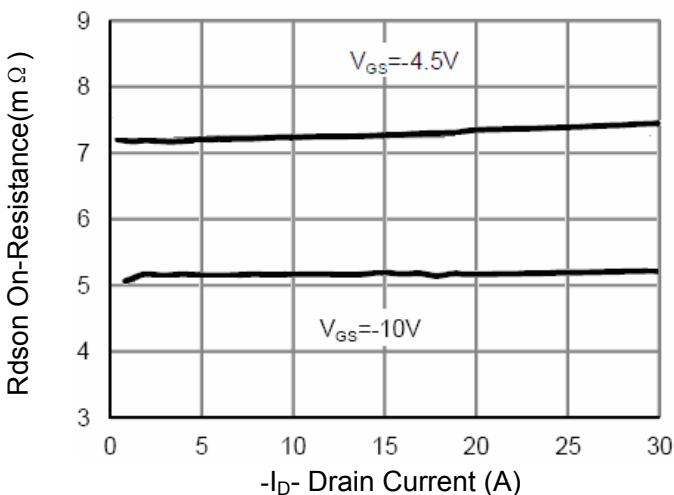
**Figure 4 Rdson-Junction Temperature**



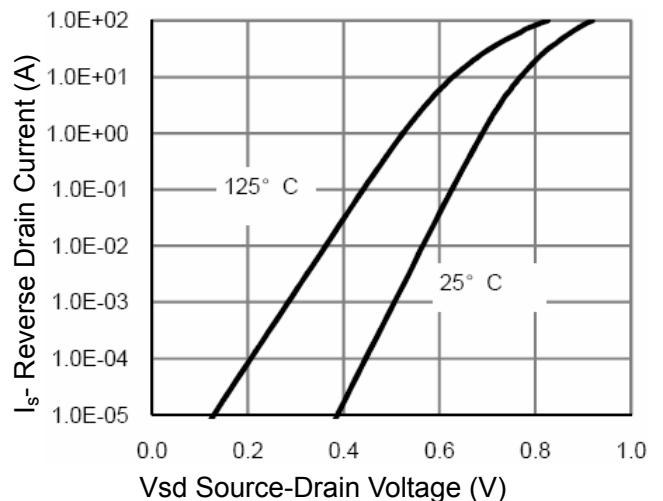
**Figure 2 Transfer Characteristics**



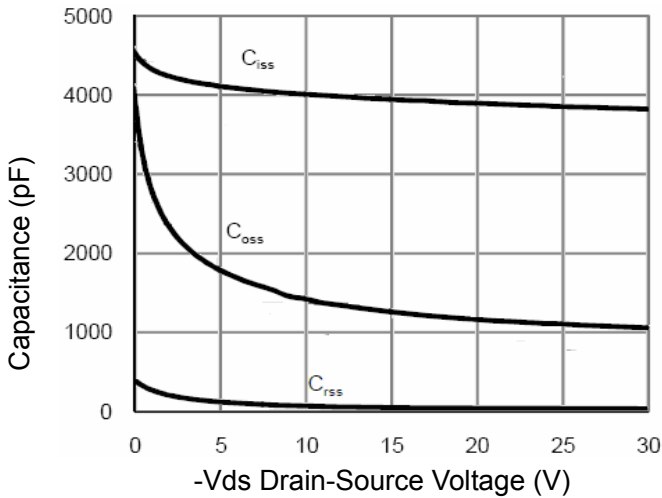
**Figure 5 Gate Charge**



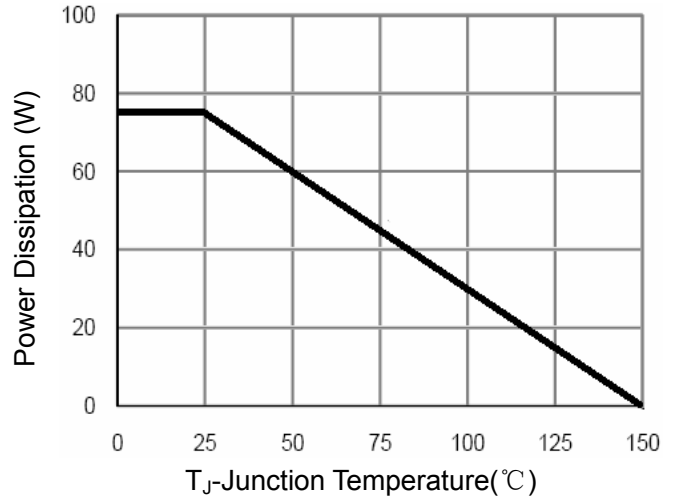
**Figure 3 Rdson- Drain Current**



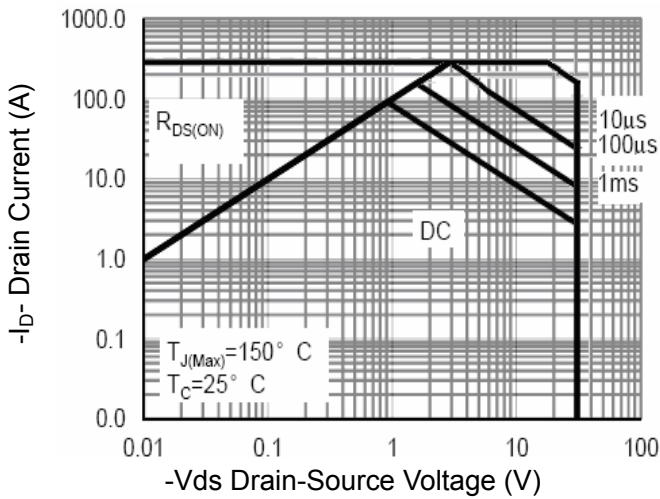
**Figure 6 Source- Drain Diode Forward**



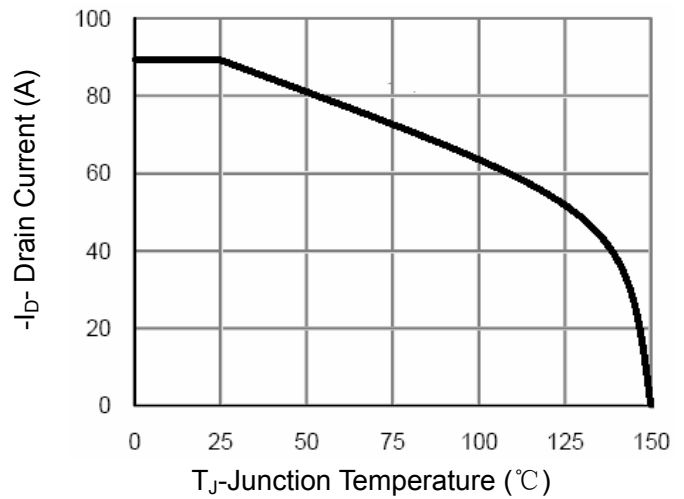
**Figure 7 Capacitance vs Vds**



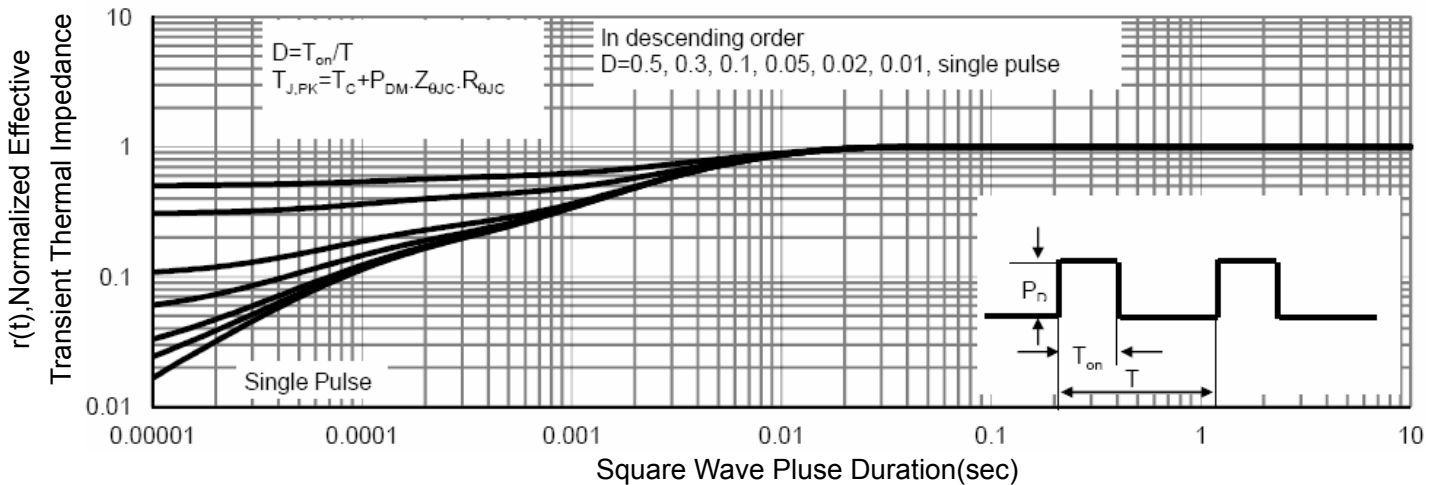
**Figure 9 Power De-rating**



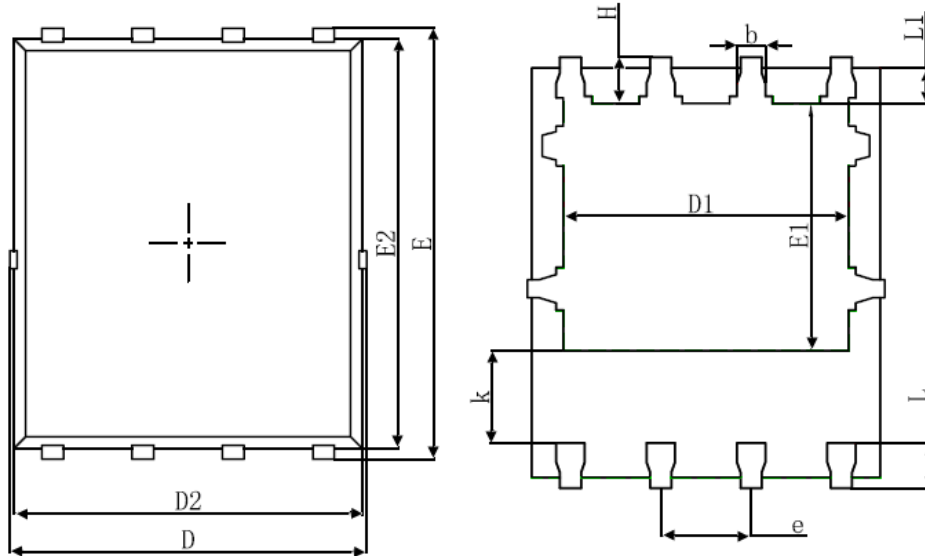
**Figure 8 Safe Operation Area**



**Figure 10 Current De-rating**



**Figure 11 Normalized Maximum Transient Thermal Impedance**

**DFN5X6-8L Package Information**


Top View  
[顶视图]

Bottom View  
[背视图]

Side View  
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
$\theta$	8°	12°	8°	12°

Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time
Pb device	245°C ±5°C	5sec ±1sec
Pb-Free device	260°C +0/-5°C	5sec ±1sec



This integrated circuit can be damaged by ESD. UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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